

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	60	igarashi near yusuke.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:10
2	BRS	L2	70	mizuhara near hideki.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:11
3	BRS	L3	421	sakamoto near noriaki.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:13

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	2718	438/106.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:14
5	BRS	L5	39	4 and (third near conductive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:22
6	BRS	L6	7627	(third near conductive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	33	((etch\$3) near (first near conductive)) near25 (third near conductive)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/11/08 11:40
8	BRS	L8	6157	((etch\$3) near (conductive))	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/11/08 11:41
9	BRS	L9	864	((etch\$3) near (conductive)) near25 (remov\$3)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/11/08 11:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	50	((etch\$3) near (conductive)) near25 (remov\$3) near35 (resin or fill\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:45
11	BRS	L11	2	((etch\$3 or pattern\$3) near (conductive)) near25 (remov\$3 near5 third near conductive) near35 (resin or fill\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:47
12	BRS	L12	8	((etch\$3 or pattern\$3) near (conductive)) near25 (remov\$3 near5 third near conductive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 11:51

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	205	((etch\$3 or pattern\$3)) near25 (remov\$3 near5 third near conductive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:07
14	BRS	L14	15743	((etch\$3 or pattern\$3)) near25 (remov\$3) near35 (resin or fill\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:09
15	BRS	L15	15	((etch\$3 or pattern\$3)) near25 (remov\$3) near20 (anchor) near35 (resin or fill\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:08

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	1513	((etch\$3 or pattern\$3)) near25 (remov\$3) near35 (resin or fill\$3) near15 (semiconductor)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:33
17	BRS	L17	4847	((etch\$3 or pattern\$3)) near25 (remov\$3) near35 (resin or fill\$3) near15 (mask or resist or photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:34
18	BRS	L18	384	((etch\$3 or pattern\$3)) near25 (remov\$3) near35 (resin or fill\$3) near15 (mask or resist or photoresist) near15 (electrode\$1)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 8 12:34

	U	1	Document ID	Title	Current OR
1			US 20040097081 A1	Method for manufacturing circuit devices	438/689
2			US 20040092129 A1	Method for manufacturing circuit devices	438/754
3			US 20020008599 A1	Multi-layer microwave circuits and methods of manufacture	333/128
4			US 6525623 B2	Multi-layer microwave circuits and methods of manufacture	333/128
5			US 5733708 A	Multilayer e-beam lithography on nonconducting substrates	430/296
6			US 5438013 A	Method of making a semiconductor memory device having a capacitor	438/396
7			JP 08330420 A	CONTACT HOLE FORMING METHOD	
8	X		JP 04015923 A	SEMICONDUCTOR DEVICE AND MANUFACTURE OF SAME	